



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



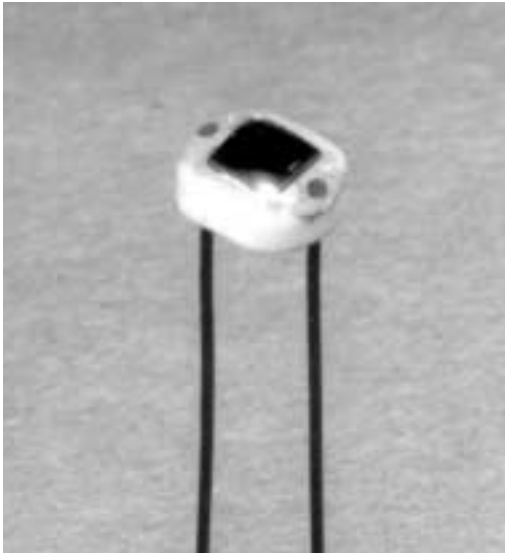
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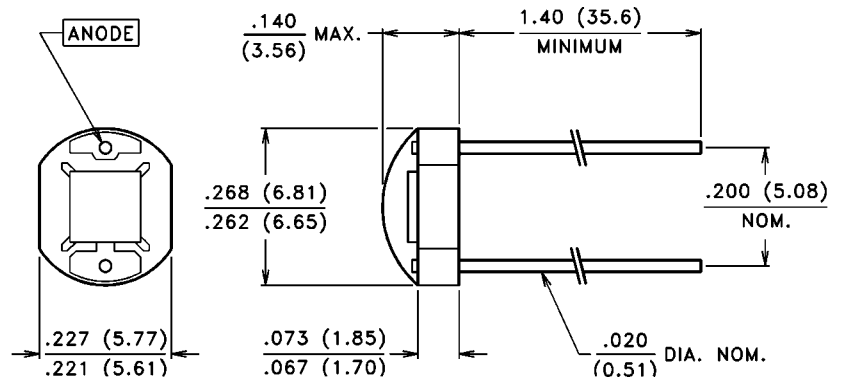
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PACKAGE DIMENSIONS inch (mm)



CASE 11 CERAMIC
CHIP ACTIVE AREA: .012 in² (7.45 mm²)

PRODUCT DESCRIPTION

Planar silicon photodiode mounted on a two lead ceramic substrate and coated with a thick layer of clear epoxy. These diodes exhibit low dark current under reverse bias and fast speed of response.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -20°C to 75°C
Operating Temperature: -20°C to 75°C

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, pages 45-46)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTP8350H			UNITS
			Min.	Typ.	Max.	
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	65	80		μA
TC I _{SC}	I _{SC} Temperature Coefficient	2850 K		.20		%/°C
V _{OC}	Open Circuit Voltage	H = 100 fc, 2850 K		350		mV
TC V _{OC}	V _{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I _D	Dark Current	H = 0, V _R = 10 V			30	nA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		100		GΩ
C _J	Junction Capacitance	H = 0, V = 3 V			50	pF
Re	Responsivity	940 nm		.06		A/(W/cm ²)
S _R	Sensitivity	@ Peak		.55		A/W
λ _{range}	Spectral Application Range		400		1150	nm
λ _p	Spectral Response - Peak			925		nm
V _{BR}	Breakdown Voltage		33	140		V
θ _{1/2}	Angular Resp. - 50% Resp. Pt.			±60		Degrees
NEP	Noise Equivalent Power			1.8 x 10 ⁻¹³ (Typ.)		W/√Hz
D*	Specific Detectivity			1.5 x 10 ¹² (Typ.)		cm√Hz/W